

SBR2040CT SBR2040CTF SBR2040CTI SBR2040CTB

Super Barrier Rectifier TM

Using state-of-the-art SBR IC process technology, the following features are made possible in a single device:

Major ratings and characteristics

Characteristics	Values	Units
$I_{F(AV)}$ Rectangular Waveform	20	А
V _{RRM}	40	V
V _F @10A, Tj=125 ⁰ C	0.43	V, typ
Tj (operating/storage)	-65 to 150	°C

ELECTRICAL:

- * Low Forward Voltage Drop
- * Reliable High Temperature Operation
- * Super Barrier Design
- * Softest, fast switching capability
- * 150°C Operating Junction Temperature

Device optimized for low forward voltage drop to maximize efficiency in Power Supply applications

MECHANICAL:

* Molded Plastic TO-220AB, TO-262, TO-263, and ITO-220 packages

Case Styles					
SBR2040CT	SBR2040CTF	SBR2040CTI	SBR2040CTB		
			Sec.		
Anode 1 Cathode Anode	2 Common Cathode Anode	Anode Common 3 Anode Anode	2 Common Anode 1 Cathode 3 Anode		
TO-220AB	ITO-220	TO-262	TO-263		



Maximum Ratings and Electrical Cha (at 25 ⁰ C unless otherwise specified)	racteristic	s		
	SYMBOL			UNITS
DC Blocking Voltage Working Peak Reverse Voltage Peak Repetitive Reverse Voltage	V _{rm} V _{rwm} V _{rrm}	40		Volts
Average Rectified Forward Current (Rated V _R -20Khz Square Wave) - 50% duty cycle	I _o	20		Amps
Peak Forward Surge Current - 1/2 60hz	I _{FSM}	120		Amps
Peak Repetitive Reverse Surge Current (2uS-1Khz)	I _{RRM}	2		Amps
Instantaneous Forward Voltage (per leg) $I_F = 10A; T_J = 25^{\circ}C$ $I_F = 10A; T_J = 125^{\circ}C$	V _F	Тур 	Max 0.53 0.48	Volts
Maximum Instantaneous Reverse Current at Rated V_{RM} $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	I _R *	Тур 	Max 0.5 100	mA mA
Maximum Rate of Voltage Change (at Rated V_R)	dv/dt	10,000		V/uS
Maximum Thermal Resistance JC (per leg) Package = TO-220AB, TO-262, & TO-263 Package = ITO-220	Rθ _{JC}	2 4		°C/W
Operating and Storage Junction Temperature	TJ	-65 to +150		°C

NOTE: Dice are available for customer applications.

* Pulse width < 300 uS, Duty cycle < 2%

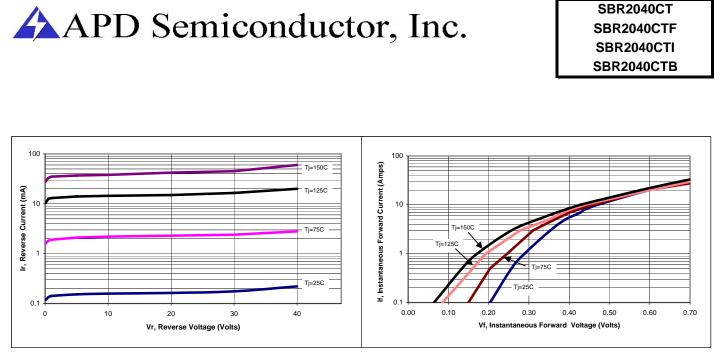


Figure 1: Typical Reverse Current

Figure 2: Typical Forward Voltage

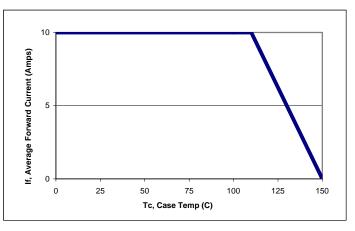


Figure 3: Current Derating, Case

APD SEMICONDUCTOR reserves the right to make changes without further notice to any products herein. APD SEMICONDUCTOR makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does APD SEMICONDUCTOR assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Typical "parameters which may be provided in APD SEMICONDUCTOR data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. APD SEMICONDUCTOR does not convey any license under its patent rights nor the rights of others. APD SEMICONDUCTOR products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to surgical injury or detath may cotter application, by systems intended for surgical injury or detath may cotter. Should Buyer purchase or use APD SEMICONDUCTOR products for any such unintended or unauthorized application, Buyer shall indemnify and hold APD SEMICONDUCTOR and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees anising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized due use, even if such claim all claims.

APD Semiconductor, Inc.

1 Lagoon Drive, Suite 410, Redwood City, CA 94065, USA Ph: 650 508 8896 FAX: 650 508 8865 Homepage: www.apdsemi.com email: info@apdsemi.com